





## **BAV16W SCHOTTKY BARRIER DIODE**



### **Features**

- Fast switching speed
- Surface mount package ideally suited for automatic insertion
- For general purpose switching applications
- High conductance
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

# **Circuit Diagram**



### **Mechanical Data**

- Case: SOD-123, Molded Plastic
- Terminals: Plated leads Solderable per MIL-STD-202,
  - Method 208
- Polarity: Cathode Band
- Weight: 0.01 grams(approx.)
- Marking: T6

### Maximum Ratings @T<sub>A</sub>=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	Limit	Units
Non-Repetitive Peak Reverse Voltage	V <sub>RM</sub>	75	V
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	100	V
RMS Reverse Voltage	$V_{R(RMS)}$	71	V
Forward Continuous Current	I <sub>FM</sub>	300	mA
Average Rectified Output Current	lo	150	mA
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I <sub>FSM</sub>	2	А
Power Dissipation	P <sub>d</sub>	400	mW
Typical Thermal Resistance Junction to Ambient	R <sub>θJA</sub>	250	°C/W
Junction Temperature Range	TJ	150	°C
Storage Temperature Range	T <sub>STG</sub>	-55 to +150	°C

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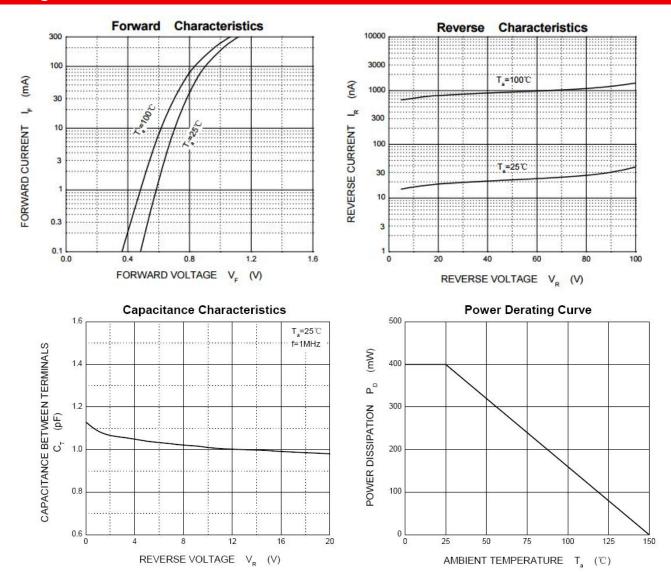


# Electrical Characteristics @T<sub>A</sub>=25°C unless otherwise specified

Characteristic	Symbol	Max	Unit	Test Condition
Forward Voltage*	V <sub>F</sub>	0.715 0.855 1.0 1.25	V	I <sub>F</sub> =1mA I <sub>F</sub> =10mA I <sub>F</sub> =50mA I <sub>F</sub> =150mA
Reverse Leakage Current*	I <sub>R</sub>	1	μA	V <sub>R</sub> =75V
Capacitance between terminals	Ст	2	pF	V <sub>R</sub> =0V,f=1.0MHz
Reverse recovery time	t <sub>rr</sub>	4	ns	$I_F = I_R = 10$ mA, $I_{rr} = 0.1 \times I_R$ , $R_L = 100$ $\Omega$

<sup>\*</sup> Pulse width < 300  $\mu$ s, duty cycle < 2%

### **Ratings and Characteristics Curves**



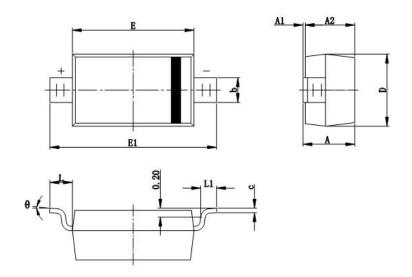
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# **Mechanical Dimensions SOD-123**



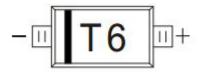
0)44501	Millimeters		Inches	
SYMBOL	MIN.	MAX.	MIN.	MAX.
Α	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.450	0.650	0.018	0.026
С	0.080	0.150	0.003	0.006
D	1.500	1.700	0.059	0.067
Е	2.600	2.800	0.102	0.110
E1	3.550	3.850	0.140	0.152
L	0.500 REF.		0.020	REF.
L1	0.250	0.450	0.010	0.018
θ	0°	8°	0°	8°

# **Ordering Information**

Device	Package	Shipping
BAV16W	SOD-123	3000pcs / reel
DAVIOV	(Pb-Free)	3000pcs / Teel

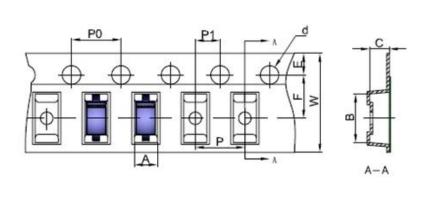
For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

# **Marking Diagram**



T6 = Marking code

# **Carrier Tape Specification SOD-123**



SYMBOL	Millimeters		
STINIBUL	Min.	Max.	
Α	1.80	1.90	
В	3.89	3.99	
С	1.52	1.62	
d	1.45	1.65	
E	1.65	1.85	
F	3.40	3.60	
Р	3.90	4.10	
P0	3.90	4.10	
P1	1.90	2.10	
W	7.90	8.30	

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